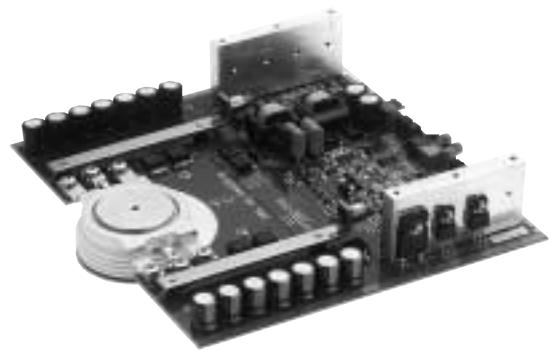


MITSUBISHI GCT (Gate Commutated Turn-off) THYRISTOR UNIT

GCU04AA-130

HIGH POWER INVERTER USE PRESS PACK TYPE

GCU04AA-130



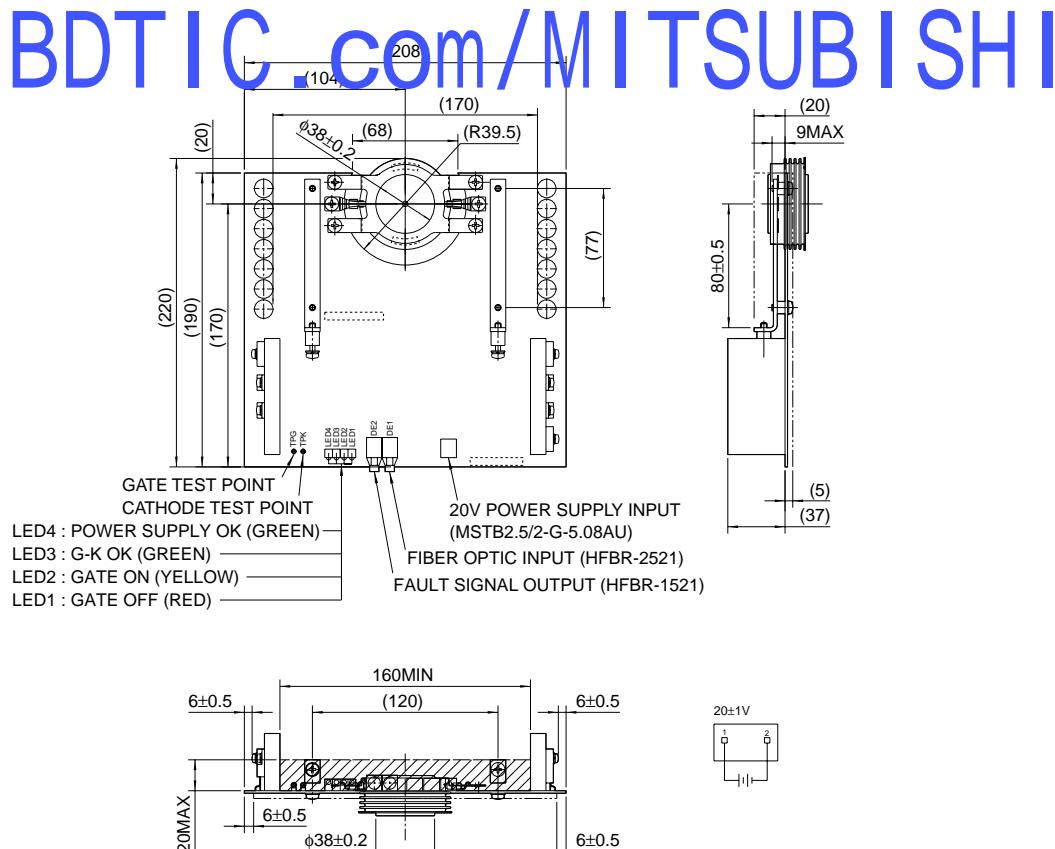
- Symmetrical GCT unit
 - GCT and gate driver are connected
 - IT_{QRM} : Repetitive controllable on-state current 400A
 - IT_{AV} : Average on-state current 180A
 - V_{DRM} : Repetitive peak off-state voltage 6500V
 - V_{RRM} : Repetitive peak reverse voltage 6500V
 - T_j : Operation junction temperature 125°C

APPLICATION

Current source inverters, DC choppers, Induction heaters, DC to DC converter

OUTLINE DRAWING

Dimensions in mm



GCT PART**MAXIMUM RATINGS**

Symbol	Parameter	Conditions	Voltage class	Unit
V _{RRM}	Repetitive peak reverse voltage	—	6500	V
V _{RSM}	Non-repetitive peak reverse voltage	—	6500	V
V _{DRM}	Repetitive peak off-state voltage	Gate driver energized	6500	V
V _{DSDM}	Non-repetitive peak off-state voltage	Gate driver energized	6500	V
V _(LTDS)	Long term DC stability voltage	Gate driver energized, $\lambda = 100$ Fit	3600	V

Symbol	Parameter	Conditions	Ratings	Unit
I _{T(RMS)}	RMS on-state current	Applied for all condition angles	280	A
I _{T(AV)}	Average on-state current	f = 60Hz, sinewave $\theta = 180^\circ$, T _f = 55°C	180	A
I _{TQRM}	Repetitive controllable on-state current	V _{DM} = 4000V, V _D = 3000V, L _C = 0.3μH T _j = 25/125°C (See Fig. 1, 3)	400	A
I _{TSM}	Surge on-state current	One half cycle at 60Hz, T _j = 125°C start	2.8	kA
I _{t²}	Current-squared, time integration	One half cycle at 60Hz, T _j = 125°C start	3.3 × 10 ⁴	A ² s
dI/dt	Critical rate of rise of on-state current	V _D = 3000V, I _T = 400A, C _S = 0.06μF, R _S = 15Ω T _j = 25/125°C, f = 60Hz (See Fig. 1, 2)	1000	A/μs
dI/dt	Critical rate of rise of reverse recovery current	I _T = 400A, V _R = 3000V, T _j = 25/125°C C _S = 0.06μF, R _S = 15Ω (See Fig. 4, 5)	1000	A/μs
P _{FGM}	Peak forward gate power dissipation		3	kW
P _{RGFM}	Peak reverse gate power dissipation		9	kW
P _{F(G)} (AV)	Average forward gate power dissipation		50	W
P _{R(G)} (AV)	Average reverse gate power dissipation		60	W
V _{FGM}	Peak forward gate voltage		10	V
V _{RGFM}	Peak reverse gate voltage		21	V
I _{FGM}	Peak forward gate current		250	A
I _{RGM}	Peak reverse gate current		400	A

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ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	Limits			Unit
			Min	Typ	Max	
V _{TM}	On-state voltage	I _T = 400A, T _j = 125°C	—	—	7.5	V
I _{RRM}	Repetitive peak reverse current	V _{RM} = 6500V, T _j = 125°C	—	—	150	mA
I _{DRM}	Repetitive peak off-state current	V _{DM} = 6500V, T _j = 125°C, Gata driver energized	—	—	100	mA
I _{GRM}	Reverse gate current	V _{RG} = 21V, T _j = 125°C	—	—	50	mA
dV/dt	Critical rate of rise of off-state voltage	V _D = 3000V, T _j = 125°C Gate driver energized (Expo. wave)	3000	—	—	V/μs
t _{GT}	Turn-on time	I _T = 400A, V _D = 3000V, dI/dt = 1000A/μs	—	—	5	μs
t _{TD}	Turn-on delay time	C _S = 0.06μF, R _S = 15Ω, T _j = 125°C (See Fig. 1, 2)	—	—	1	μs
E _{on}	Turn-on switching energy		—	—	0.7	J/P
t _S	Storage time	I _T = 400A, V _{DM} = 4000V, V _D = 3000V	—	—	3	μs
E _{off}	Turn-off switching energy	C _S = 0.06μF, R _S = 15Ω, T _j = 125°C (See Fig. 1, 5)	—	—	2.9	J/P
Q _{RR}	Reverse recovery charge	V _R = 3000V, I _T = 400A, dI/dt = 1000A/μs	—	—	1600	μC
E _{rec}	Reverse recovery energy	C _S = 0.06μF, R _S = 15Ω, T _j = 125°C (See Fig. 4, 5)	—	—	4.1	J/P
I _{GT}	Gate trigger current	V _D = 24V, R _L = 0.1Ω, T _j = 25°C	—	—	0.35	A
V _{GT}	Gate trigger voltage	DC method	—	—	1.5	V

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**HIGH POWER INVERTER USE
PRESS PACK TYPE**

GATE DRIVER PART

Symbol	Parameter	Conditions	Limits			Unit
			Min	Typ	Max	
VGIN	Power supply voltage	DC power supply	19	20	21	V
PGIN	Gate power consumption	I _G = 230Arms, f = 780Hz, duty = 0.33	—	—	20	W
t _{fd}	Delay time of on gate current	T _a = 25°C	—	—	3.0	μs
t _{rd}	Delay time of off gate current	T _a = 25°C	—	—	3.0	μs
—	Control signal	Optical fiber data link Transmitter : HFBR-1521 : Agilent Receiver : HFBR-2521 : Agilent	—	—	—	—
—	Power supply connector	Phoenix contact Type name : MSTB25/2-G-508AU	—	—	—	—
—	Status signal	—	(Note 1)		—	—

MECHANICAL DATA

Symbol	Parameter	Conditions	Limits			Unit
			Min	Typ	Max	
F _M	Mounting force	—	7.3	8.6	11	kN
—	Weight	—	—	700	—	g
—	Pole piece diameter (GTC device)	±0.2mm	—	38	—	mm
—	Housing thickness (GTC device)	±0.5mm	—	26	—	mm

THERMAL DATA

Symbol	Parameter	Conditions	Limits			Unit
			Min	Typ	Max	
T _j	Junction operating temperature	—	-10	—	125	°C
T _{stg}	Storage temperature	—	-10	—	60	°C
T _a	Ambient operation temperature	Recommend : ≤ 40°C	-10	—	60	°C
R _{t(j-f)}	Thermal resistance	Junction to Fin	—	—	0.04	K/W

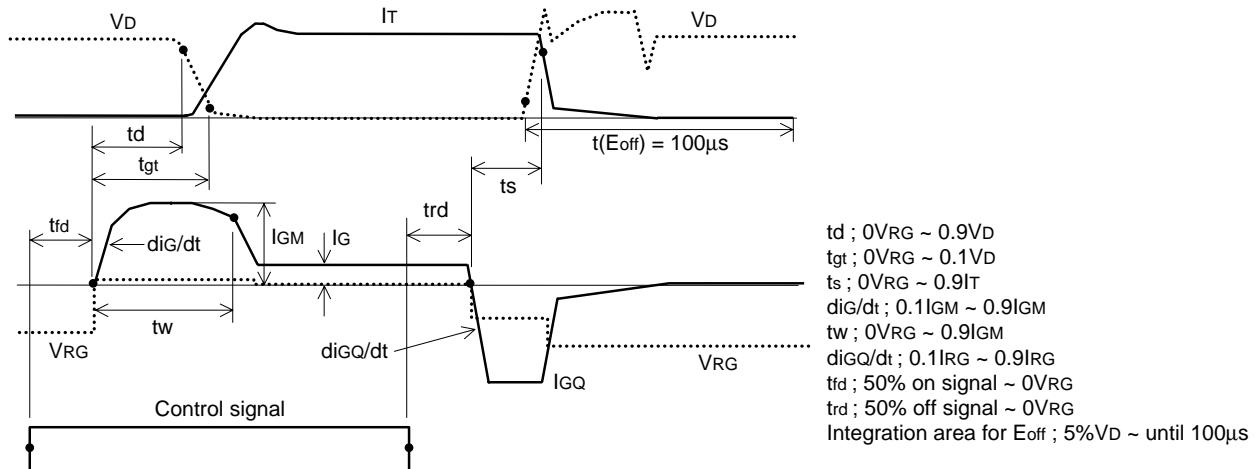


Fig. 1 Turn-on and Turn-off waveform

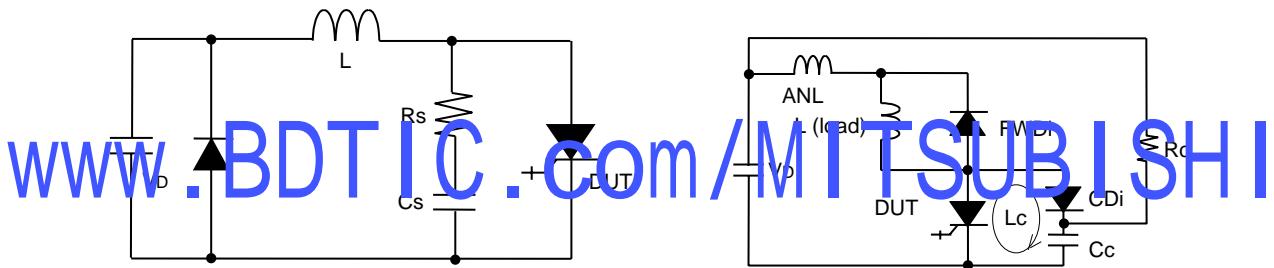


Fig. 2 Turn-on test circuit

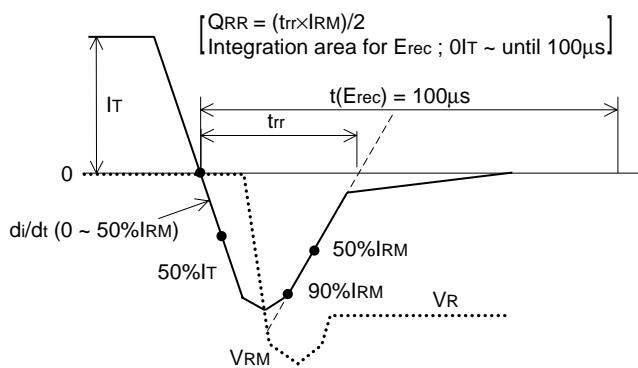
Fig. 3 Turn-off test circuit
(With clamp circuit)

Fig. 4 Reverse recovery waveform

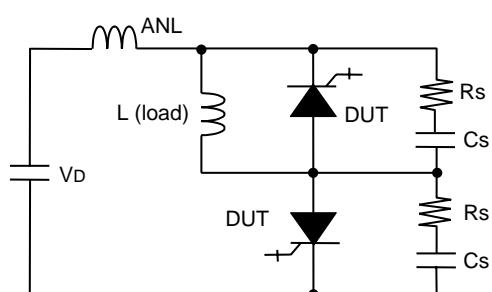


Fig. 5 Turn-off and Reverse recovery test circuit

Note 1. Status signal

1. Status signal from LED**(1) Status signal**

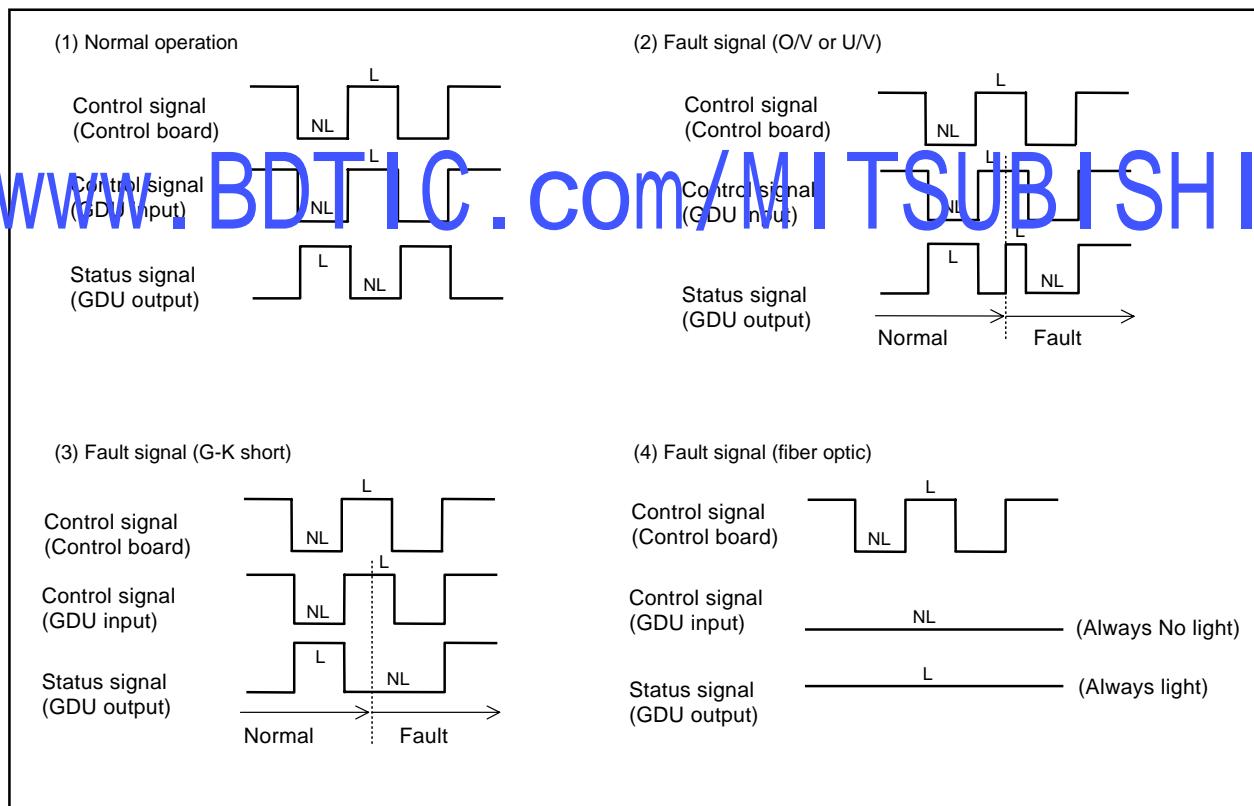
Status of GCT	LED 1 (Red)	LED 2 (Yellow)
On state	OFF	ON
Off state	ON	OFF

(2) Fault signal

Status	G-K	Power Supply	G-K LED (LED 3) (Green)	PS LED (LED 4) (Green)
Normal	Normal	20±1V	On	On
Fault	Normal	Voltage down	Off	Off
Fault	G-K short	20±1V	Off	On
Fault	G-K short	Voltage down	Off	Off

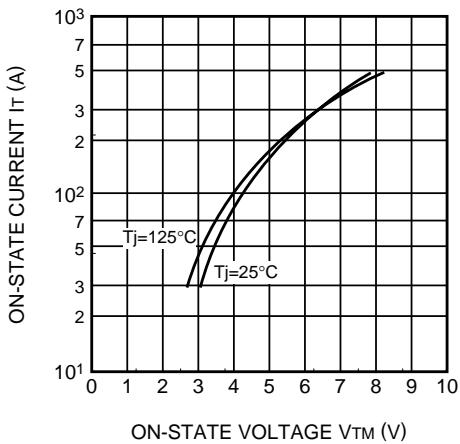
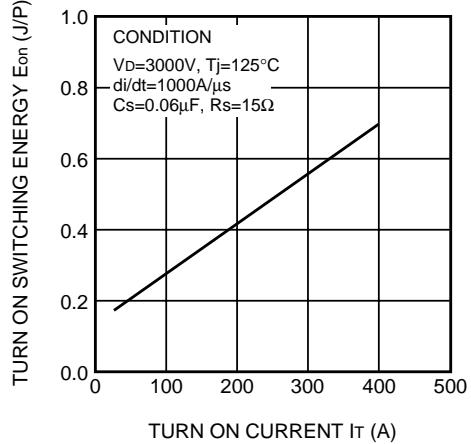
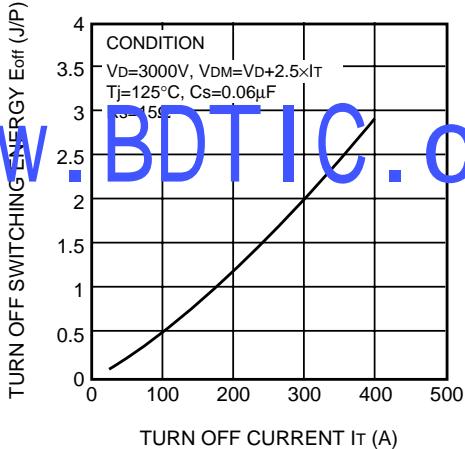
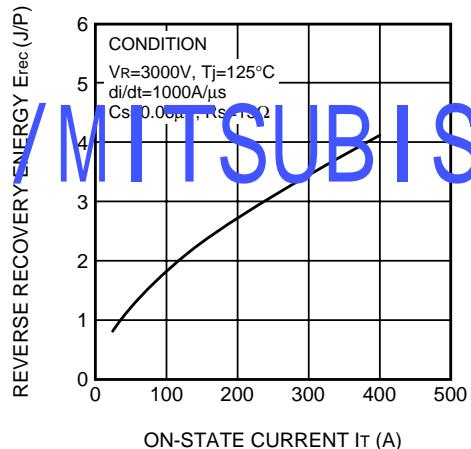
2. Status signal from Transmitter

(L : Light NL : No light)



PERFORMANCE CURVES

MAXIMUM ON-STATE CHARACTERISTIC

E_{on} VS I_T (Max)E_{off} VS I_T (Max)E_{rec} VS I_T (Max)MAXIMUM THERMAL IMPEDANCE
CHARACTERISTIC
(JUNCTION TO FIN)